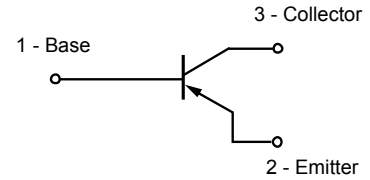


Feature

- PNP epitaxial planar silicon transistor



Mechanical Characteristics

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature:260°C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil

Absolute maximum rating@25°C

Parameter	Symbol	Value	Units
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-60	V
Emitter -Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	V
Collector Current - Continuous	$I_C$	-600	mA
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	$P_D$	225 1.8	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{qJA}$	556	°C/W
Total Device Dissipation Alumina Substrate,(2) $T_A = 25^\circ\text{C}$ Derate above 25°C	$P_D$	300 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{qJA}$	417	°C/W
Operating and Storage Junction Temperature Range	$T_J T_{Stg}$	-55to+15	°C

Electrical characteristics per line@25°C ( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF CHARACTERISTICS</b>						
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-60	-	-	V
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-10uA, I_E=0$	-60	-	-	V
Emitter -Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-10uA, I_C=0$	-5.0	-	-	V
Collector Cutoff Current	$I_{CEX}$	$(V_{CE} = -30V, V_{BE(off)} = -0.5V)$	-50	-	-	nA
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=-50V, I_E=0V$ $V_{CB}=-50V, I_E=0, T_A=125^\circ C$	-	-	-0.010 -10	$\mu A$
Base Current	$I_B$	$V_{CE}=-30V, V_{EB(off)}=-0.5V$	-	-	-50	nA
<b>ON CHARACTERISTICS</b>						
DC Current Gain	$H_{FE}$	$I_C=-0.1mA, V_{CE}=-10V$	75	-	-	-
		$I_C=-1.0mA, V_{CE}=-10V$	100	-	-	
		$I_C=-10mA, V_{CE}=-10V$	100	-	-	
		$I_C=-150mA, V_{CE}=-10V(3)$	100	-	300	
		$I_C=-500mA, V_{CE}=-10V(3)$	50	-	-	
Collector-Emitter Saturation Voltage(3)	$V_{CE(sat)}$	$I_C=-150mA, I_B=-15mA$	-	-	-0.4	V
		$I_C=-500mA, I_B=-50mA$	-	-	-1.6	
Base-Emitter Saturation Voltage(3)	$V_{BE(sat)}$	$I_C=-150mA, I_B=-15mA$	-	-	-1.3	V
		$I_C=-500mA, I_B=-50mA$	-	-	-2.6	
<b>SMALL SIGNAL CHARACTERISTICS</b>						
Current-Gain-Bandwidth Product	$f_T$	$I_C=-50mA, V_{CE}=-20V,$ $f=100MHz$	200	-	-	MHz
Output Capacitance	$C_{obo}$	$V_{CB}=-10V, I_E=0,$ $f=1.0MHz$	-	-	8.0	pF
Input Capacitance	$C_{ibo}$	$V_{EB}=-2.0V, I_C=0,$ $f=1.0MHz$	-	-	30	pF
<b>SWITCHING CHARACTERISTICS</b>						
Turn-On Time	$(V_{CC}=-30V, I_C=-150mA, I_{B1}=-15mA)$	$t_{on}$	-	-	45	ns
Delay Time		$t_d$	-	-	10	
Rise Time		$t_r$	-	-	40	
Turn-Off Time	$(V_{CC}=-6.0V, I_C=-150mA, I_{B1}=I_{B2}=-15mA)$	$t_{off}$	-	-	100	ns
Storage Time		$t_s$	-	-	80	
Fall Time		$t_f$	-	-	30	

1. FR-5 = 1.0 X 0.75 X 0.062 in.
2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.
3. Pulse Test: Pulse Width  $\leq 300 \mu s$ , Duty Cycle  $\leq 2.0\%$ .
4.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

Typical Characteristics

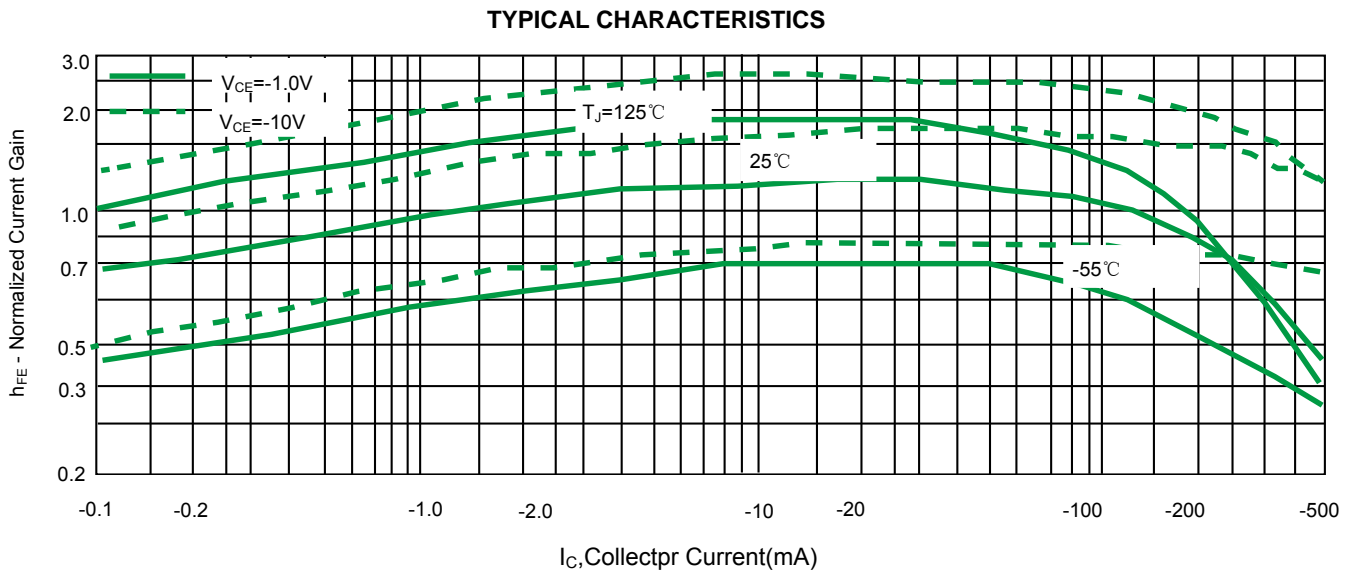


Figure1.DC Current Gain

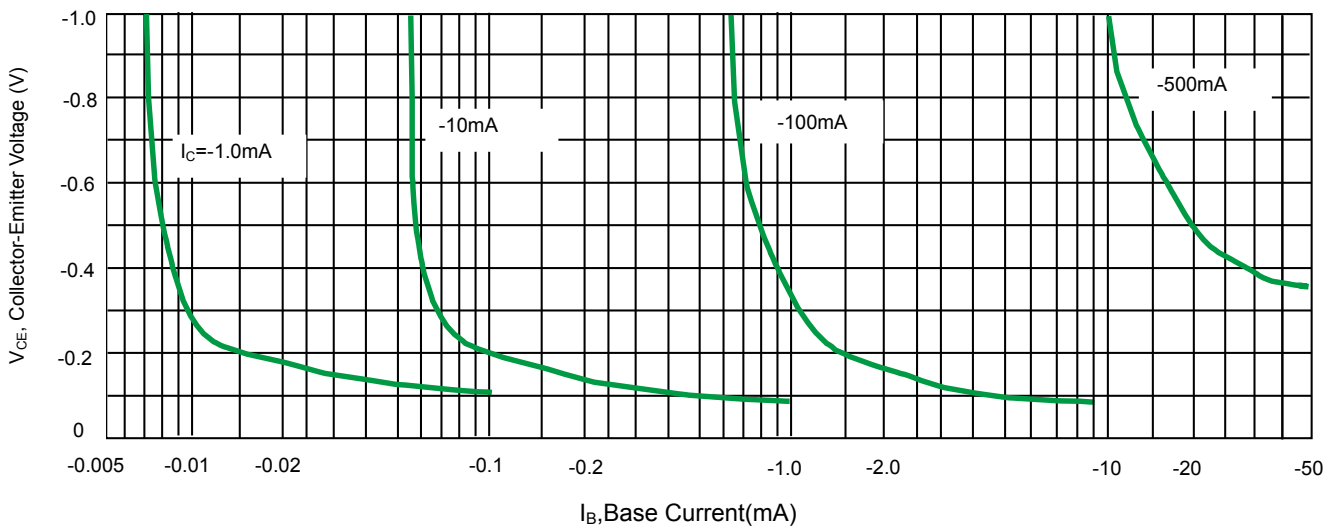


Figure2.Collector Saturation Region

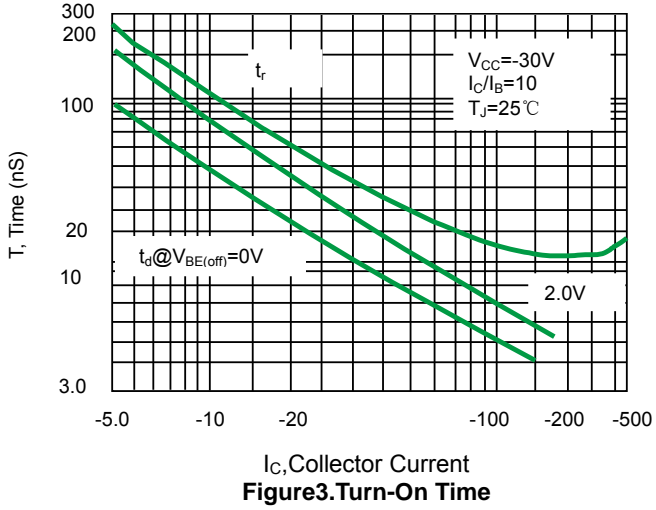


Figure3.Turn-On Time

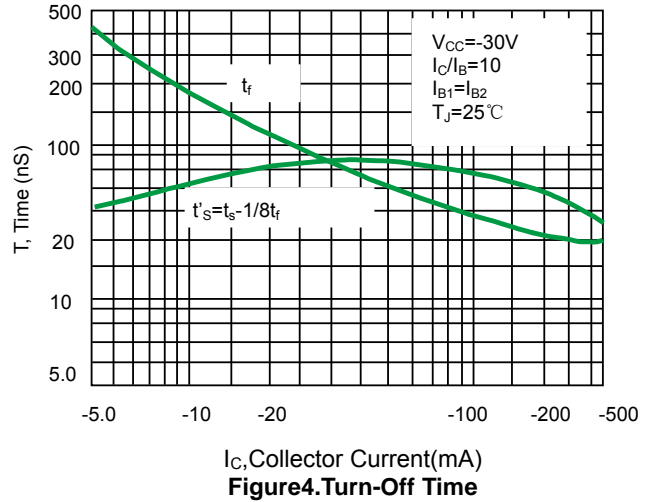


Figure4.Turn-Off Time

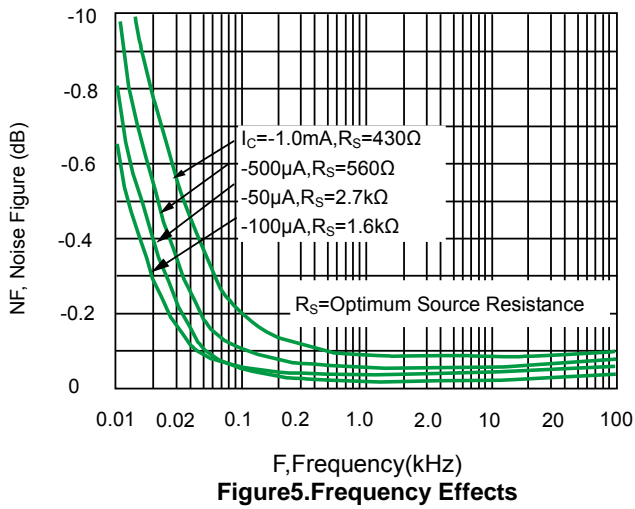


Figure5.Frequency Effects

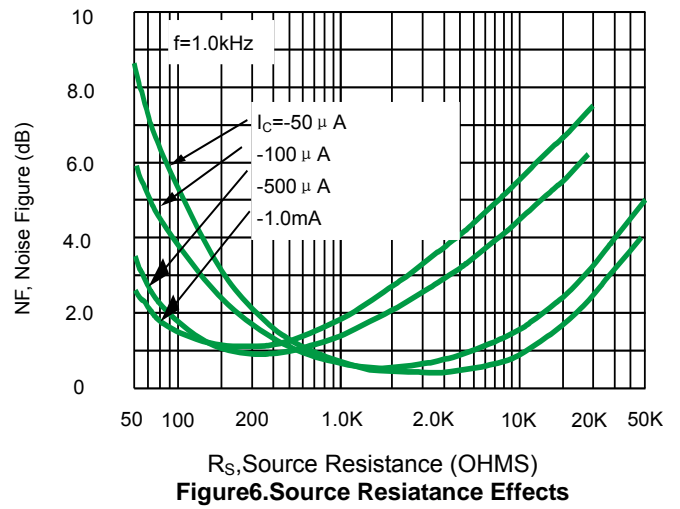


Figure6.Source Resistance Effects

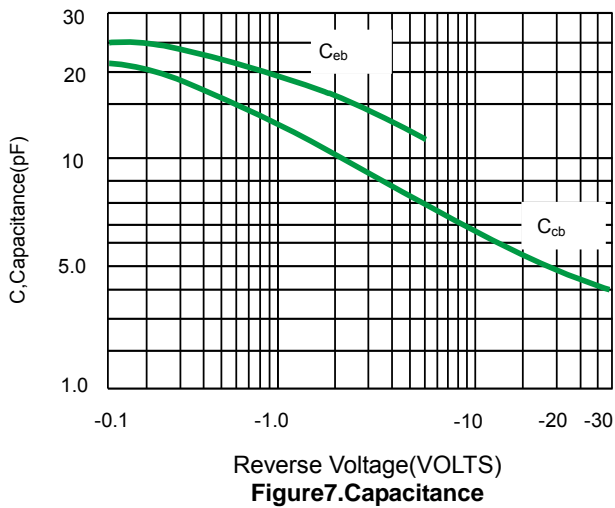


Figure7.Capacitance

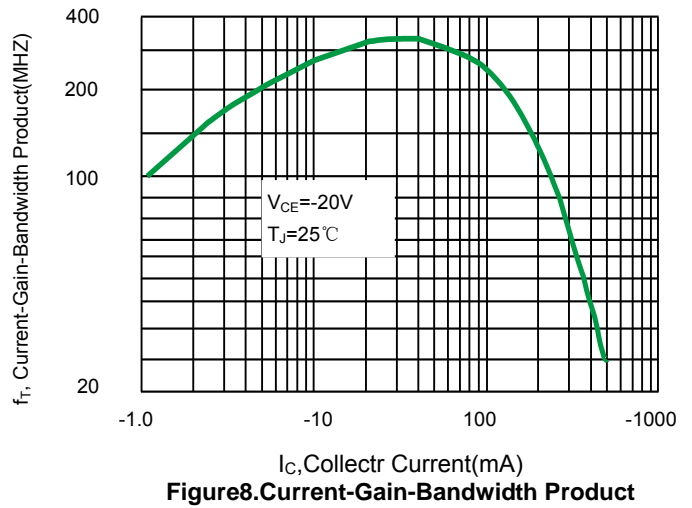
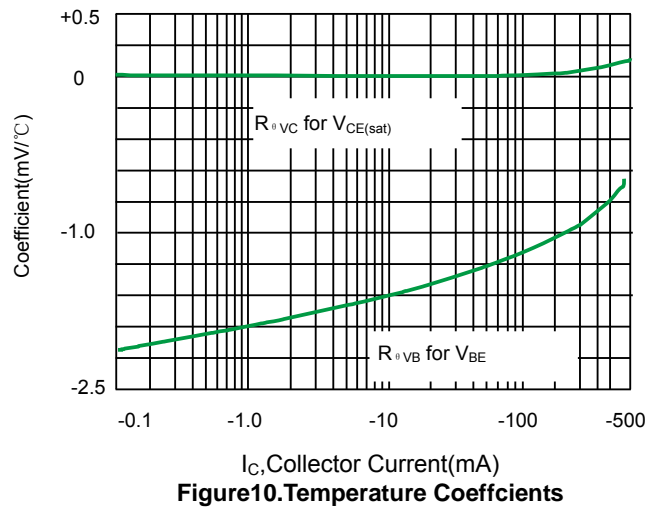
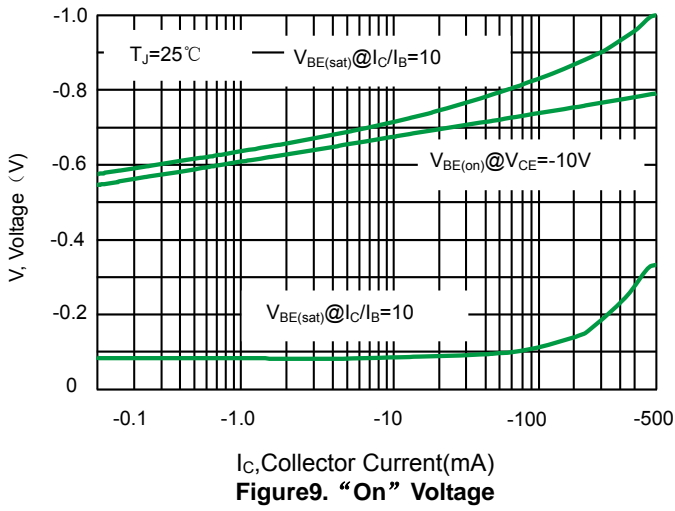
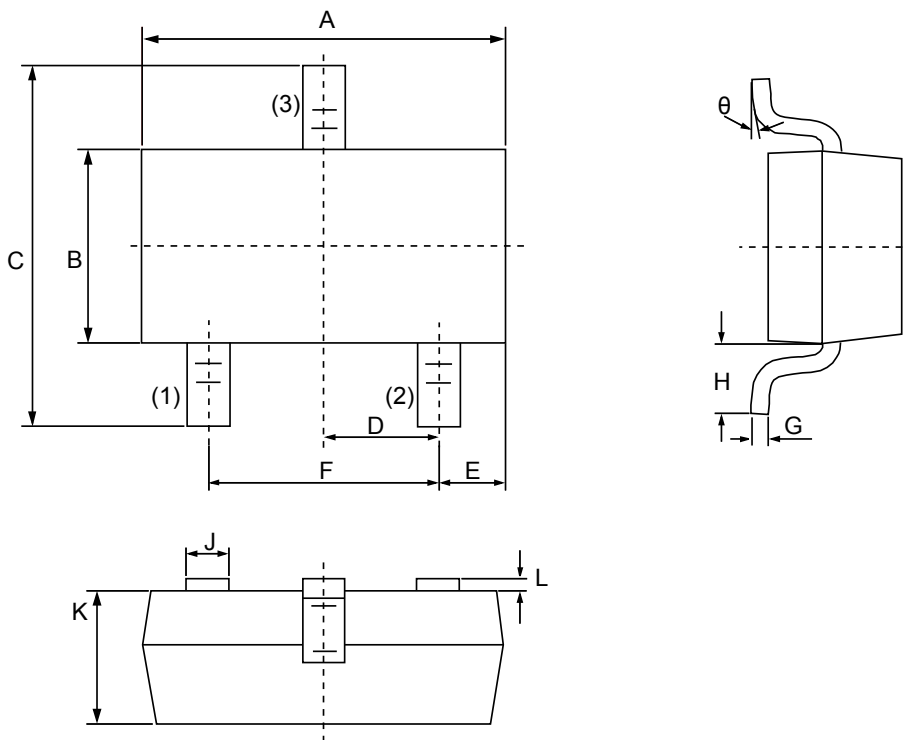


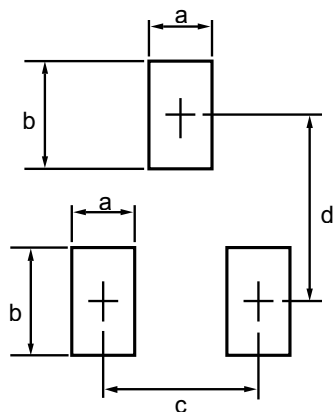
Figure8.Current-Gain-Bandwidth Product



Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
$\theta$	0°	10°	0°	10°




Dim	Millimeters	
	MIN	MAX
a	--	0.7
b	--	1.2
c	--	2.04
d	--	2.2

Ordering information

Device	Package	Shipping
PT23T2907A	SOT-23 (Pb-Free)	3000 / Tape & Reel


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